

COMPLETE LISTING OF ALL CLAIMS

1 Claim 1. (currently amended) A process for creating an electrically isolated electrode on a
2 sidewall of a cavity in a base, the process comprising the steps of:
3 etching one or more trenches in a backside of the base wherein the base is part of a
4 starting material;
5 forming a layer of insulating material on one or more sidewalls of one or more of the
6 trenches;
7 forming a conductive layer on the layer of insulating material on one or more
8 sidewalls of one or more of the trenches;
9 depositing material on or removing material from a front side of the starting material
10 that is different from the backside of the base; and;
11 removing base material from a portion of the base bordered by the one or more
12 trenches.

1 Claim 2. (original) The process of claim 1, wherein the trenches are defined underneath a
2 flap.

1 Claim 3. (original) The process of claim 1, wherein the trench etch stops on an etch-stop
2 layer.

1 Claim 4. (original) The process of claim 1, wherein the conductive layer completely fills the
2 trench.

1 Claim 5. (original) The process of claim 1, wherein a layer of conducting material is also
2 deposited on the backside of the base.

1 Claim 6. (original) The process of claim 1, wherein the trench is formed using an
2 anisotropic etch.

1 Claim 7. (original) The process of claim 1, wherein the base is a crystalline material.

1 Claim 8. (original) The process of claim 1 wherein the trench is etched such that an
2 orientation of the sidewall is defined by a crystal orientation of the base material.

1 Claim 9. (original) The process of claim 8, wherein the base is composed of crystalline
2 silicon having a <110> crystal orientation.